MBR0540-TP-FS

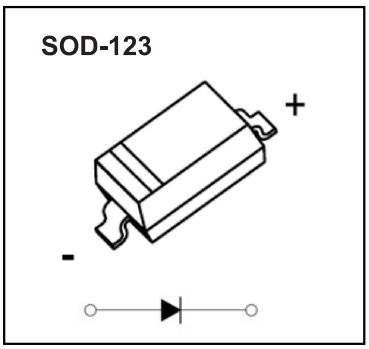
SCHOTTKY BARRIER DIODE

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- High Conductance
- Also Available in Lead Free Version

MARKING:SF





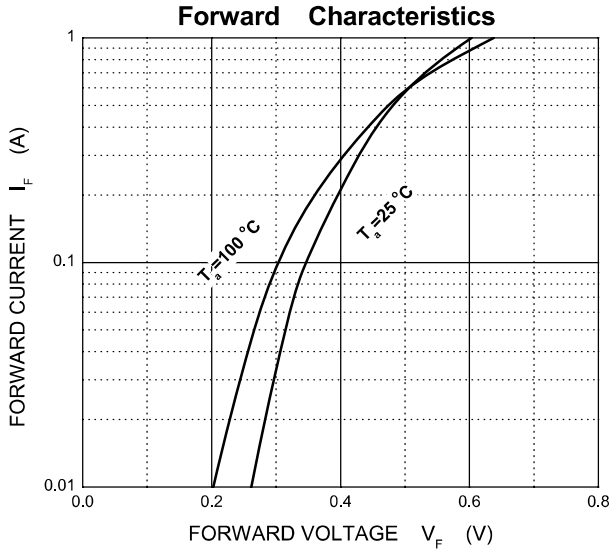
Maximum Ratings @Ta=25℃

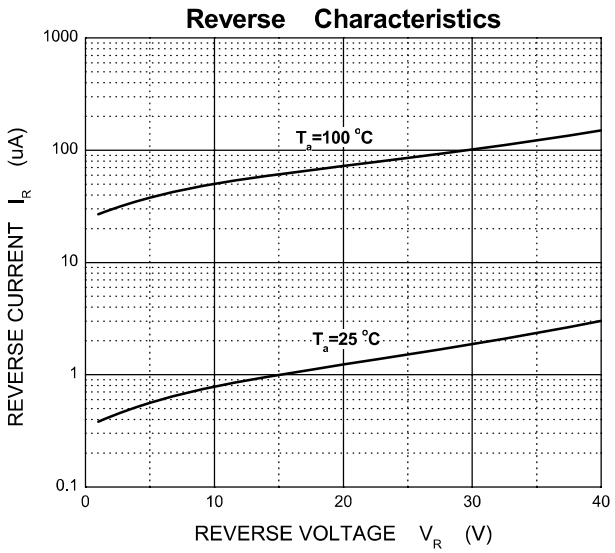
Parameter	Symbo	Value	Unit
Peak repetitive peak reverse voltage Working peak reverse voltage DC blocking voltage	V_{RRM} V_{RWM} V_R	40	V
RMS reverse voltage reverse voltage (DC)	$V_{R(RMS)}$	28	V
Average rectified output current	I_o	0.5	A
Non-repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	5.5	A
Power dissipation	P_D	500	mW
Thermal resistance junction to ambient	$R_{\theta JA}$	200	℃/W
Operating Junction Temperature Range	T_j	-40 ~ +125	℃
Storage Temperature Range	T_{STG}	-55 ~ +150	℃
Voltage rate of change	dv/dt	1000	V/μs

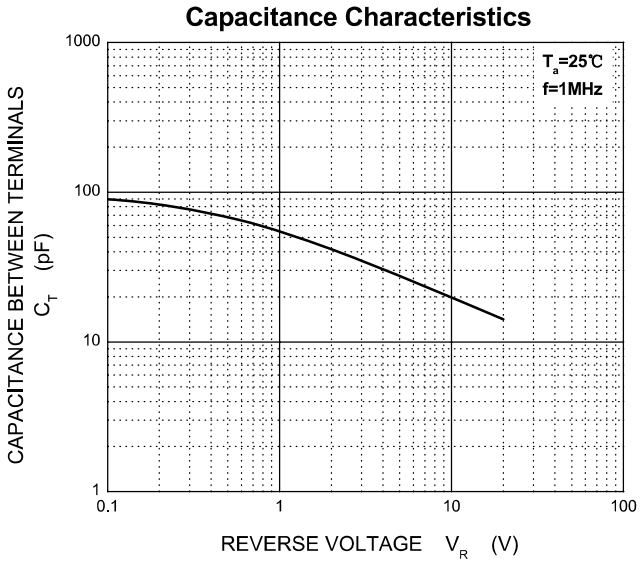
Electrical Characteristics @Ta=25℃

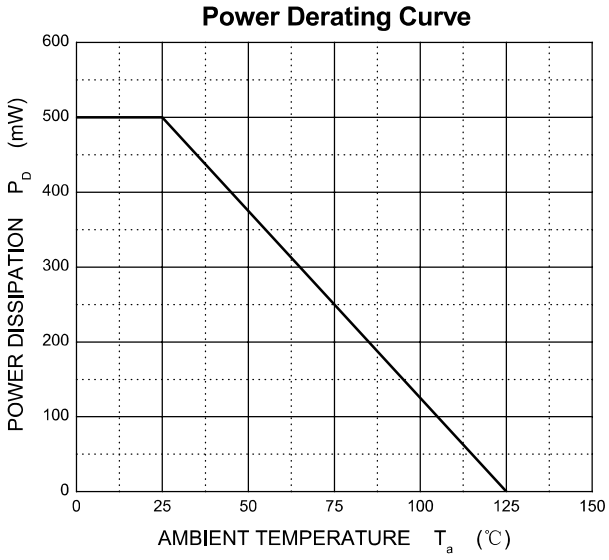
	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R=20uA	40			V
Reverse current	I_R	V_R=20V			10	uA
		V_R=40V			20	
Forward voltage	V_F	I_F=0.5A			0.51	V
		I_F=1.0A			0.62	
Capacitance between terminals	C_T	V_R=0,f=1MHz			170	pF

Typical Characteristics

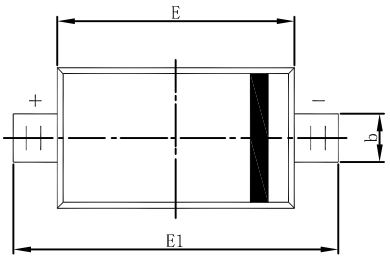


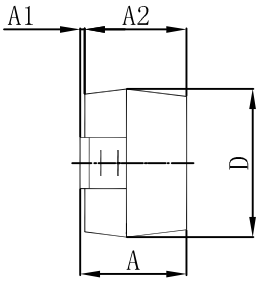


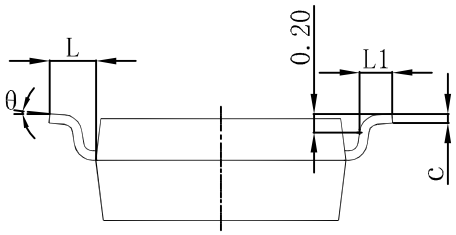




SOD-123 Package Outline Dimensions

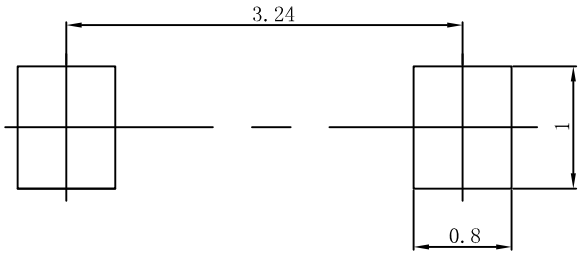






Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.450	0.650	0.018	0.026
c	0.080	0.150	0.003	0.006
D	1.500	1.700	0.059	0.067
E	2.600	2.800	0.102	0.110
E1	3.550	3.850	0.140	0.152
L	0.500 REF		0.020 REF	
L1	0.250	0.450	0.010	0.018
θ	0°	8°	0°	8°

SOD-123 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.